

# MJD6039, NJVMJD6039T4G

## Darlington Power Transistors

### DPAK For Surface Mount Applications

Designed for general purpose power and switching such as output or driver stages in applications such as switching regulators, convertors, and power amplifiers.

#### Features

- Lead Formed for Surface Mount Applications in Plastic Sleeves (No Suffix)
- Straight Lead Version in Plastic Sleeves ("–1" Suffix)
- Monolithic Construction With Built-in Base-Emitter Shunt Resistors
- High DC Current Gain –  $h_{FE} = 2500$  (Typ) @  $I_C = 4.0$  Adc
- Epoxy Meets UL 94 V-0 @ 0.125 in
- ESD Ratings:
  - ♦ Human Body Model,  $3B > 8000$  V
  - ♦ Machine Model,  $C > 400$  V
- NJV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- Pb-Free Package is Available\*

#### MAXIMUM RATINGS

| Rating                                                                                         | Symbol         | Max           | Unit                     |
|------------------------------------------------------------------------------------------------|----------------|---------------|--------------------------|
| Collector-Emitter Voltage                                                                      | $V_{CEO}$      | 80            | Vdc                      |
| Collector-Base Voltage                                                                         | $V_{CB}$       | 80            | Vdc                      |
| Emitter-Base Voltage                                                                           | $V_{EB}$       | 5             | Vdc                      |
| Collector Current Continuous Peak                                                              | $I_C$          | 4<br>8        | Adc                      |
| Base Current                                                                                   | $I_B$          | 100           | mAdc                     |
| Total Power Dissipation @ $T_C = 25^\circ\text{C}$<br>Derate above $25^\circ\text{C}$          | $P_D$          | 20<br>0.16    | W<br>W/ $^\circ\text{C}$ |
| Total Power Dissipation (Note 1) @ $T_A = 25^\circ\text{C}$<br>Derate above $25^\circ\text{C}$ | $P_D$          | 1.75<br>0.014 | W<br>W/ $^\circ\text{C}$ |
| Operating and Storage Junction Temperature Range                                               | $T_J, T_{stg}$ | -65 to +150   | $^\circ\text{C}$         |

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

1. These ratings are applicable when surface mounted on the minimum pad sizes recommended.

\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.



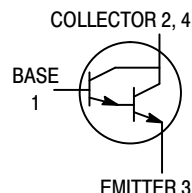
ON Semiconductor®

<http://onsemi.com>

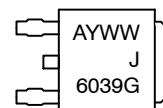
### SILICON POWER TRANSISTORS 4 AMPERES, 80 VOLTS, 20 WATTS



DPAK  
CASE 369C  
STYLE 1



#### MARKING DIAGRAM



A = Assembly Location  
Y = Year  
WW = Work Week  
J6039 = Device Code  
G = Pb-Free Package

#### ORDERING INFORMATION

| Device        | Package           | Shipping†         |
|---------------|-------------------|-------------------|
| MJD6039T4     | DPAK              | 2,500/Tape & Reel |
| MJD6039T4G    | DPAK<br>(Pb-Free) | 2,500/Tape & Reel |
| NJVMJD6039T4G | DPAK<br>(Pb-Free) | 2,500/Tape & Reel |

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

# MJD6039, NJVMJD6039T4G

## THERMAL CHARACTERISTICS

| Characteristic                                   | Symbol          | Max  | Unit                 |
|--------------------------------------------------|-----------------|------|----------------------|
| Thermal Resistance, Junction-to-Case             | $R_{\theta JC}$ | 6.25 | $^{\circ}\text{C/W}$ |
| Thermal Resistance, Junction-to-Ambient (Note 2) | $R_{\theta JA}$ | 71.4 | $^{\circ}\text{C/W}$ |

2. These ratings are applicable when surface mounted on the minimum pad sizes recommended.

## ELECTRICAL CHARACTERISTICS ( $T_C = 25^{\circ}\text{C}$ unless otherwise noted)

| Characteristic | Symbol | Min | Max | Unit |
|----------------|--------|-----|-----|------|
|----------------|--------|-----|-----|------|

### OFF CHARACTERISTICS

|                                                                                 |                |    |    |                 |
|---------------------------------------------------------------------------------|----------------|----|----|-----------------|
| Collector-Emitter Sustaining Voltage<br>( $I_C = 30 \text{ mAdc}$ , $I_B = 0$ ) | $V_{CEO(sus)}$ | 80 | –  | Vdc             |
| Collector-Cutoff Current<br>( $V_{CE} = 40 \text{ Vdc}$ , $I_B = 0$ )           | $I_{CEO}$      | –  | 10 | $\mu\text{Adc}$ |

### ON CHARACTERISTICS (Note 3)

|                                                                                                                                 |               |             |        |     |
|---------------------------------------------------------------------------------------------------------------------------------|---------------|-------------|--------|-----|
| DC Current Gain<br>( $I_C = 1 \text{ Adc}$ , $V_{CE} = 4 \text{ Vdc}$ )<br>( $I_C = 2 \text{ Adc}$ , $V_{CE} = 4 \text{ Vdc}$ ) | $h_{FE}$      | 1000<br>500 | –<br>– | –   |
| Collector-Emitter Saturation Voltage<br>( $I_C = 2 \text{ Adc}$ , $I_B = 8 \text{ mAdc}$ )                                      | $V_{CE(sat)}$ | –           | 2.5    | Vdc |
| Base-Emitter On Voltage<br>( $I_C = 2 \text{ Adc}$ , $V_{CE} = 4 \text{ Vdc}$ )                                                 | $V_{BE(on)}$  | –           | 2.8    | Vdc |

### DYNAMIC CHARACTERISTICS

|                                                                                                             |          |    |     |    |
|-------------------------------------------------------------------------------------------------------------|----------|----|-----|----|
| Small-Signal Current Gain<br>( $I_C = 0.75 \text{ Adc}$ , $V_{CE} = 10 \text{ Vdc}$ , $f = 1 \text{ kHz}$ ) | $h_{fe}$ | 25 | –   | –  |
| Output Capacitance<br>( $V_{CB} = 10 \text{ Vdc}$ , $I_E = 0$ , $f = 0.1 \text{ MHz}$ )                     | $C_{ob}$ | –  | 100 | pF |

3. Pulse Test: Pulse Width  $\leq 300 \mu\text{s}$ , Duty Cycle  $\leq 2\%$ .

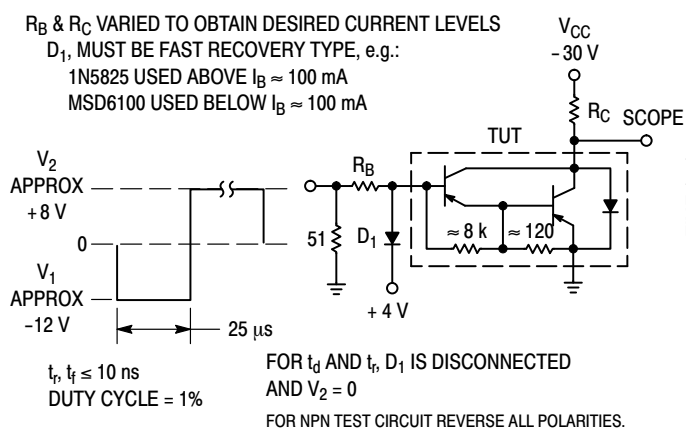


Figure 1. Switching Times Test Circuit

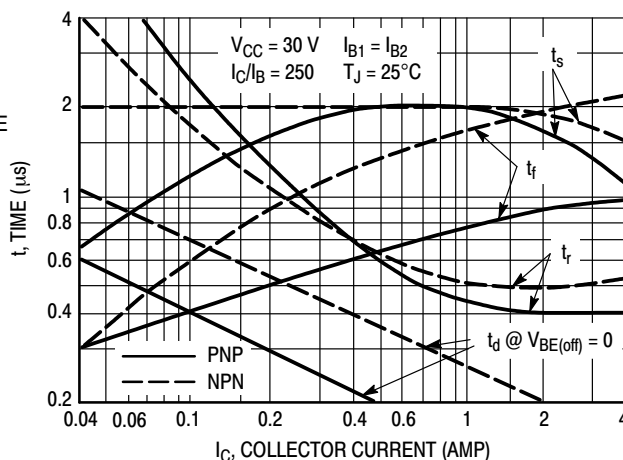


Figure 2. Switching Times

# TYPICAL ELECTRICAL CHARACTERISTICS

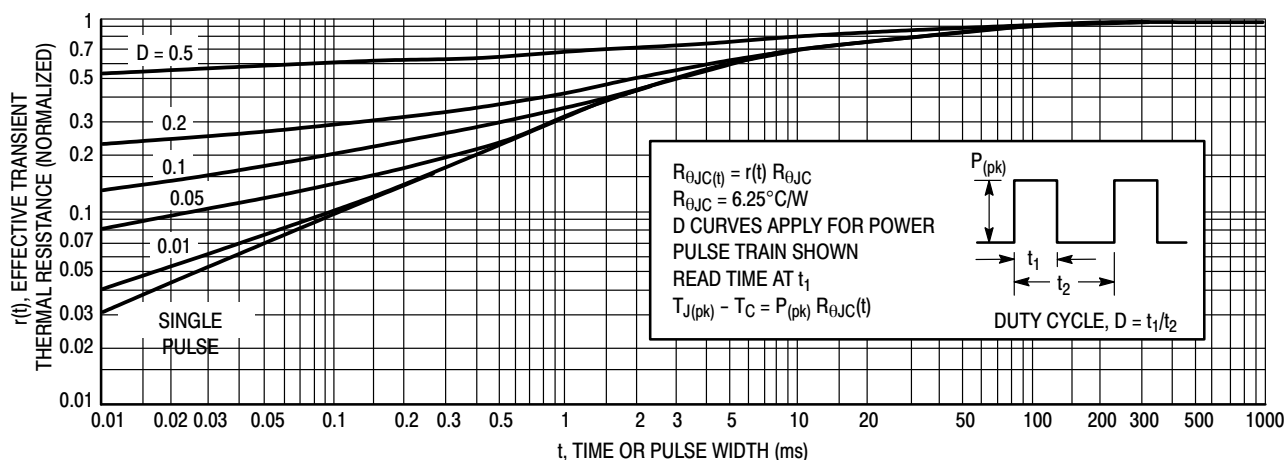


Figure 3. Thermal Response

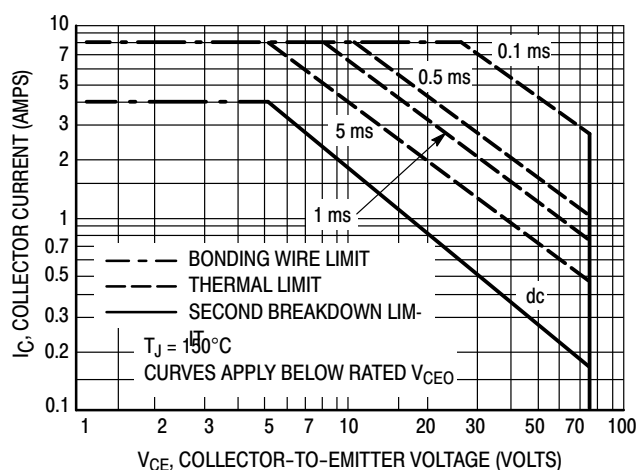


Figure 4. Maximum Rated Forward Biased Safe Operating Area

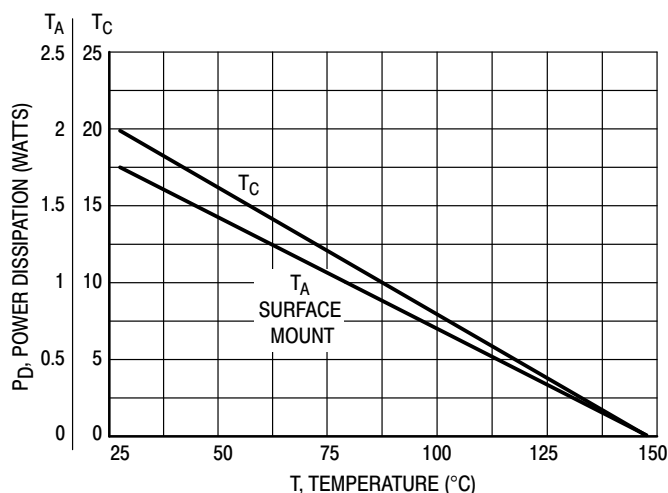


Figure 5. Power Derating

There are two limitations on the power handling ability of a transistor: average junction temperature and second breakdown. Safe operating area curves indicate  $I_C - V_{CE}$  limits of the transistor that must be observed for reliable operation; i.e., the transistor must not be subjected to greater dissipation than the curves indicate.

The data of Figures 6 and 7 is based on  $T_{J(pk)} = 150^\circ\text{C}$ ;  $T_C$  is variable depending on conditions. Second breakdown pulse limits are valid for duty cycles to 10% provided  $T_{J(pk)} < 150^\circ\text{C}$ .  $T_{J(pk)}$  may be calculated from the data in Figure 5. At high case temperatures, thermal limitations will reduce the power that can be handled to values less than the limitations imposed by second breakdown.

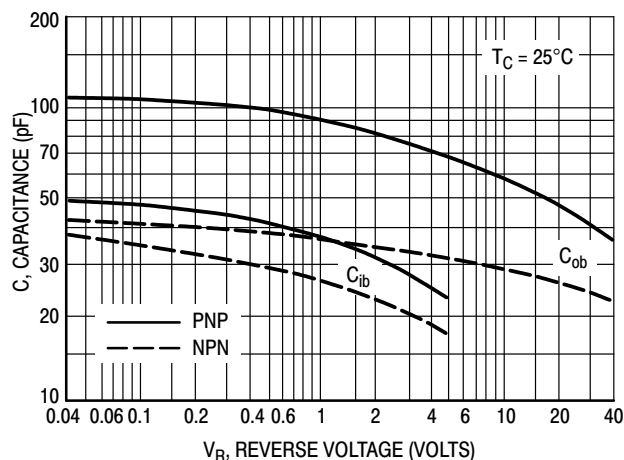


Figure 6. Capacitance

TYPICAL ELECTRICAL CHARACTERISTICS

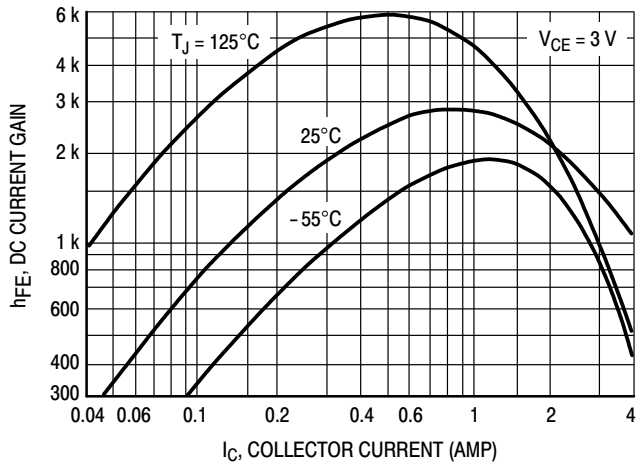


Figure 7. DC Current Gain

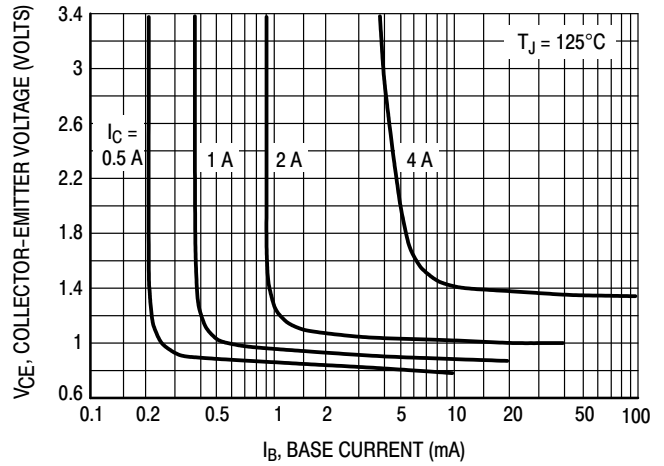


Figure 8. Collector Saturation Region

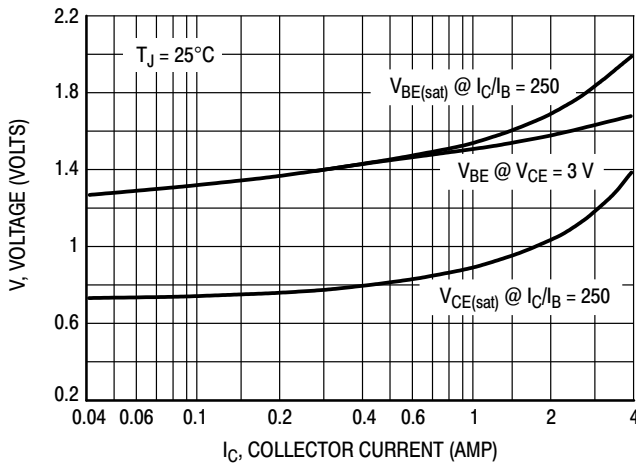


Figure 9. "On" Voltages

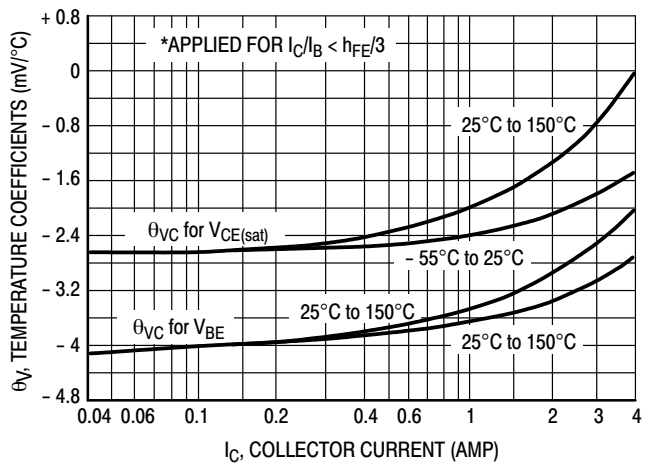


Figure 10. Temperature Coefficients

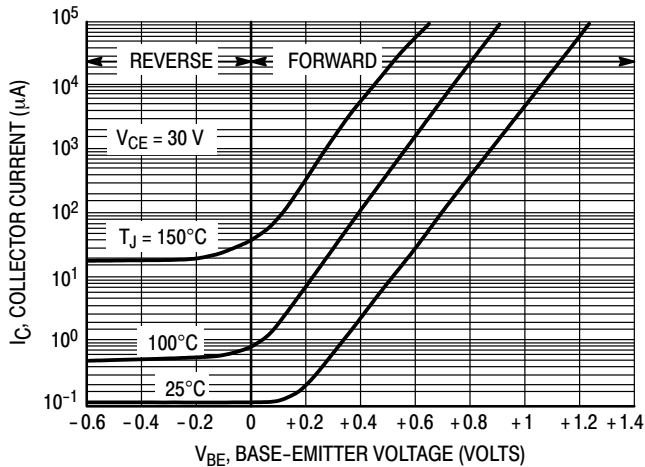


Figure 11. Collector Cut-Off Region

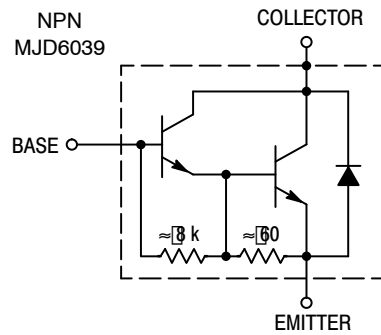
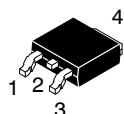


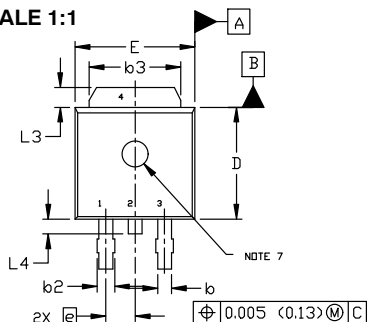
Figure 12. Darlington Schematic



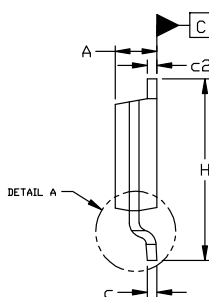
DPAK (SINGLE GAUGE)  
CASE 369C  
ISSUE G

DATE 31 MAY 2023

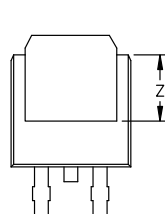
SCALE 1:1



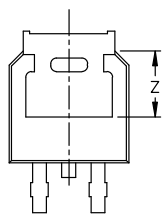
TOP VIEW



SIDE VIEW

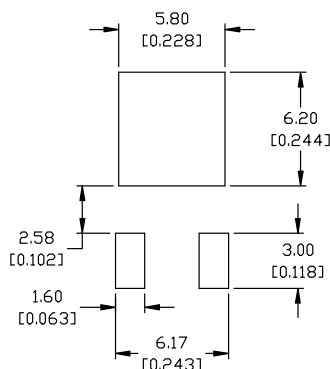


BOTTOM VIEW



BOTTOM VIEW

ALTERNATE  
CONSTRUCTIONS



RECOMMENDED MOUNTING FOOTPRINT\*

\*FOR ADDITIONAL INFORMATION ON OUR Pb-FREE STRATEGY AND SOLDERING DETAILS, PLEASE DOWNLOAD THE ON SEMICONDUCTOR SOLDERING AND MOUNTING TECHNIQUES REFERENCE MANUAL, SOLDERRM/D.

STYLE 1:

PIN 1. BASE  
2. COLLECTOR  
3. EMITTER  
4. COLLECTOR

STYLE 2:

PIN 1. GATE  
2. DRAIN  
3. SOURCE  
4. DRAIN

STYLE 3:

PIN 1. ANODE  
2. CATHODE  
3. ANODE  
4. CATHODE

STYLE 4:

PIN 1. CATHODE  
2. ANODE  
3. GATE  
4. ANODE

STYLE 5:

PIN 1. GATE  
2. ANODE  
3. CATHODE  
4. ANODE

STYLE 6:

PIN 1. MT1  
2. MT2  
3. GATE  
4. MT2

STYLE 7:

PIN 1. GATE  
2. COLLECTOR  
3. EMITTER  
4. COLLECTOR

STYLE 8:

PIN 1. N/C  
2. CATHODE  
3. ANODE  
4. CATHODE

STYLE 9:

PIN 1. ANODE  
2. CATHODE  
3. RESISTOR ADJUST  
4. CATHODE

STYLE 10:

PIN 1. CATHODE  
2. ANODE  
3. CATHODE  
4. ANODE

NOTES:

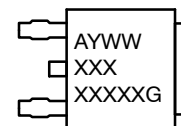
1. DIMENSIONING AND TOLERANCING ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: INCHES
3. THERMAL PAD CONTOUR OPTIONAL WITHIN DIMENSIONS b3, L3, AND Z.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR BURRS. MOLD FLASH, PROTRUSIONS, OR GATE BURRS SHALL NOT EXCEED 0.006 INCHES PER SIDE.
5. DIMENSIONS D AND E ARE DETERMINED AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY.
6. DATUMS A AND B ARE DETERMINED AT DATUM PLANE H.
7. OPTIONAL MOLD FEATURE.

| DIM | INCHES |       | MILLIMETERS |       |
|-----|--------|-------|-------------|-------|
|     | MIN.   | MAX.  | MIN.        | MAX.  |
| A   | 0.086  | 0.094 | 2.18        | 2.38  |
| A1  | 0.000  | 0.005 | 0.00        | 0.13  |
| b   | 0.025  | 0.035 | 0.63        | 0.89  |
| b2  | 0.028  | 0.045 | 0.72        | 1.14  |
| b3  | 0.180  | 0.215 | 4.57        | 5.46  |
| c   | 0.018  | 0.024 | 0.46        | 0.61  |
| c2  | 0.018  | 0.024 | 0.46        | 0.61  |
| D   | 0.235  | 0.245 | 5.97        | 6.22  |
| E   | 0.250  | 0.265 | 6.35        | 6.73  |
| e   | 0.090  | BSC   | 2.29        | BSC   |
| H   | 0.370  | 0.410 | 9.40        | 10.41 |
| L   | 0.055  | 0.070 | 1.40        | 1.78  |
| L1  | 0.114  | REF   | 2.90        | REF   |
| L2  | 0.020  | BSC   | 0.51        | BSC   |
| L3  | 0.035  | 0.050 | 0.89        | 1.27  |
| L4  | ----   | 0.040 | ---         | 1.01  |
| Z   | 0.155  | ----  | 3.93        | ---   |

GENERIC  
MARKING DIAGRAM\*



IC



Discrete

XXXXXX = Device Code  
A = Assembly Location  
L = Wafer Lot  
Y = Year  
WW = Work Week  
G = Pb-Free Package

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

|                  |                     |                                                                                                                                                                                  |
|------------------|---------------------|----------------------------------------------------------------------------------------------------------------------------------------------------------------------------------|
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onsemi Website: [www.onsemi.com](http://www.onsemi.com)

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